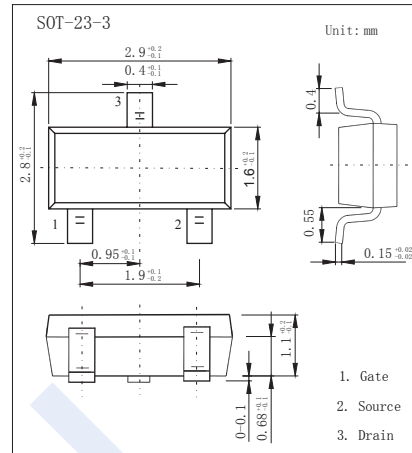
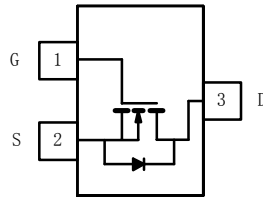


## N-Channel Enhancement MOSFET

### SI2328DS (KI2328DS)

#### ■ Features

- $V_{DS} (V) = 100V$
- $I_D = 1.5 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 250m\Omega (V_{GS} = 4.5V)$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	5 sec	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	100		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150^\circ C$ ) *1	$I_D$	$T_a = 25^\circ C$	1.5	1.15	A
		$T_a = 70^\circ C$	1.2	0.92	
Pulsed Drain Current *2	$I_{DM}$	6		mJ	
Avalanche Current *2	$I_{AS}$	6			
Single Avalanche Energy	$E_{AS}$	1.8		W	
Power Dissipation *1	$P_D$	$T_a = 25^\circ C$	1.25		0.73
		$T_a = 70^\circ C$	0.8	0.47	
Thermal Resistance. Junction- to-Ambient *1 $t \leq 5$ sec Steady State	$R_{thJA}$	100		$^\circ C/W$	
		170			
Thermal Resistance. Junction-to-Foot	$R_{thJF}$	55		$^\circ C$	
Junction Temperature	$T_J$	150			
Storage Temperature Range	$T_{stg}$	-55 to 150			

\*1 Surface Mounted on 1" x 1" FR4 Board.

\*2 Pulse width limited by maximum junction temperature

## N-Channel Enhancement MOSFET

### SI2328DS (KI2328DS)

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	100			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, Ta=70°C			75	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA	2		4	V
On-State Drain Current *1	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 15 V, V <sub>GS</sub> = 10 V	6			A
Static Drain-Source On-Resistance *1	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.5A		195	250	mΩ
Forward Transconductance *1	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =1.5A		4		S
Gate Resistance	R <sub>g</sub>		0.5		2.4	Ω
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =1.5A		3.3	4	nC
Gate Source Charge	Q <sub>gs</sub>			0.47		
Gate Drain Charge	Q <sub>gd</sub>			1.45		
Turn-On DelayTime	t <sub>d(on)</sub>	I <sub>D</sub> =0.2A, V <sub>DS</sub> =50V, V <sub>GEN</sub> =10V R <sub>L</sub> =33Ω, R <sub>G</sub> =6Ω		7	11	ns
Turn-On Rise Time	t <sub>r</sub>			11	17	
Turn-Off DelayTime	t <sub>d(off)</sub>			9	15	
Turn-Off Fall Time	t <sub>f</sub>			10	15	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.5A, di/dt= 100A/μs		50	100	
Maximum Body-Diode Continuous Current	I <sub>S</sub>				1.0	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V		0.8	1.2	V

\*1 Pulse test: PW ≤ 300us duty cycle ≤ 2%.

#### ■ Marking

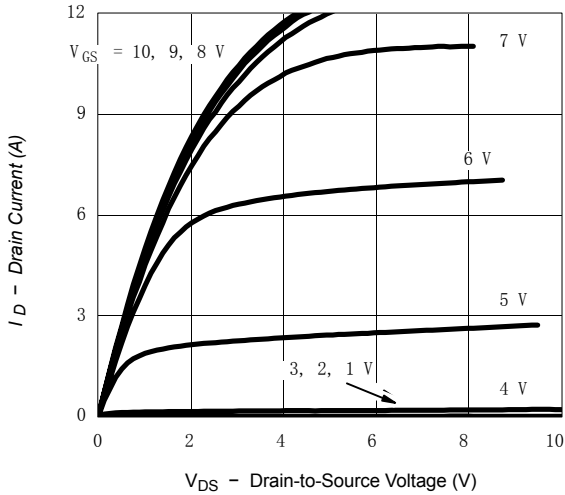
Marking	D8*
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## N-Channel Enhancement MOSFET

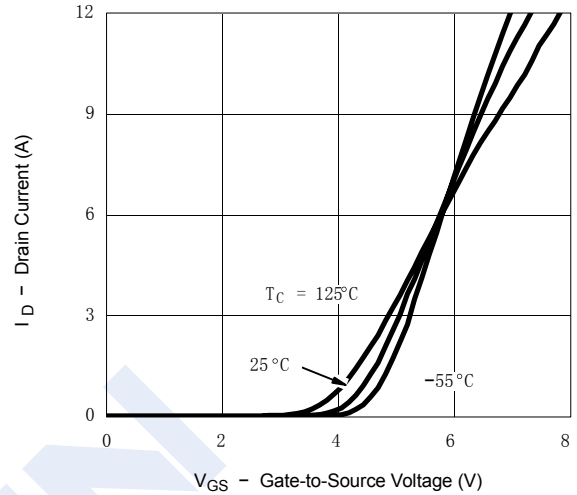
### SI2328DS (KI2328DS)

■ Typical Characteristics

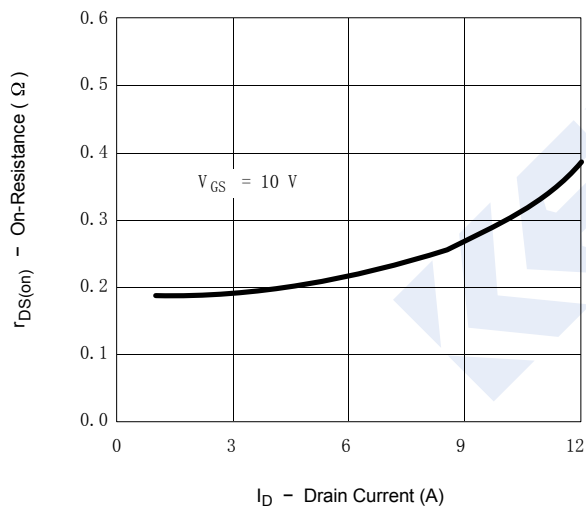
Output Characteristics



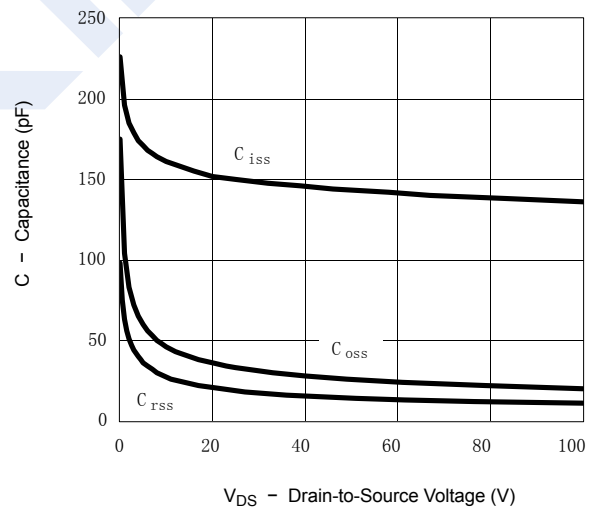
Transfer Characteristics



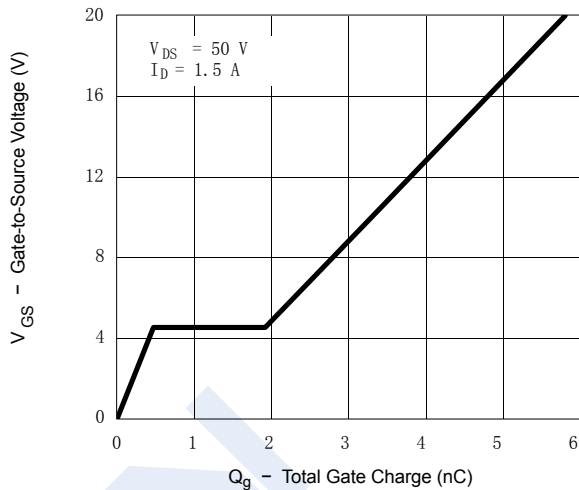
On-Resistance vs. Drain Current



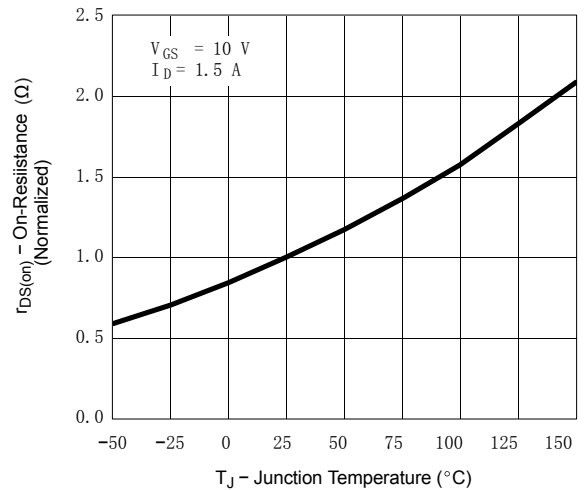
Capacitance



Gate Charge



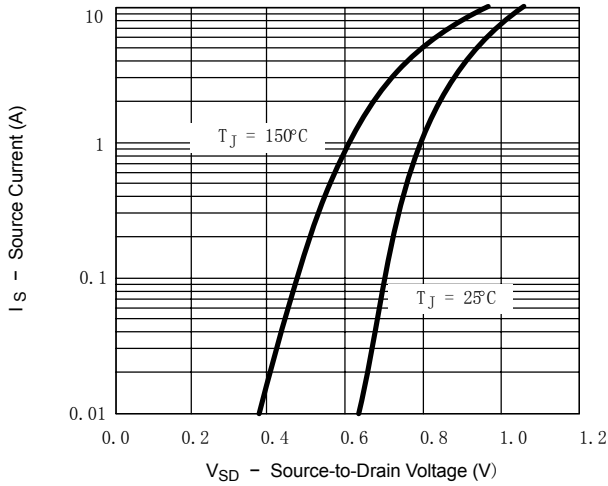
On-Resistance vs. Junction Temperature



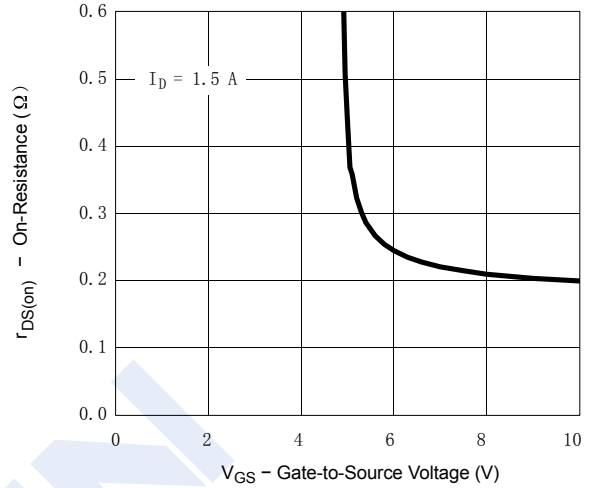
## N-Channel Enhancement MOSFET SI2328DS (KI2328DS)

■ Typical Characteristics

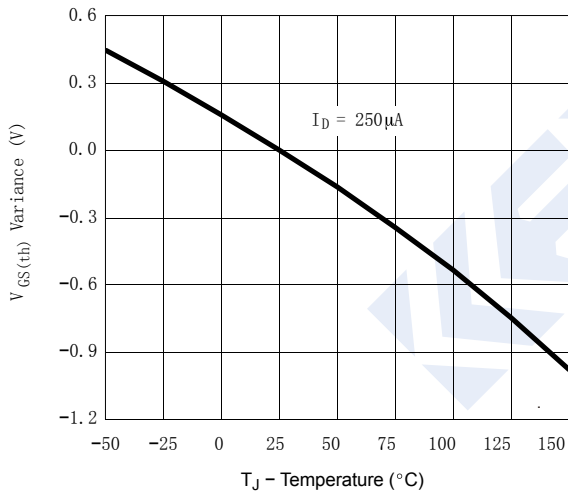
Source-Drain Diode Forward Voltage



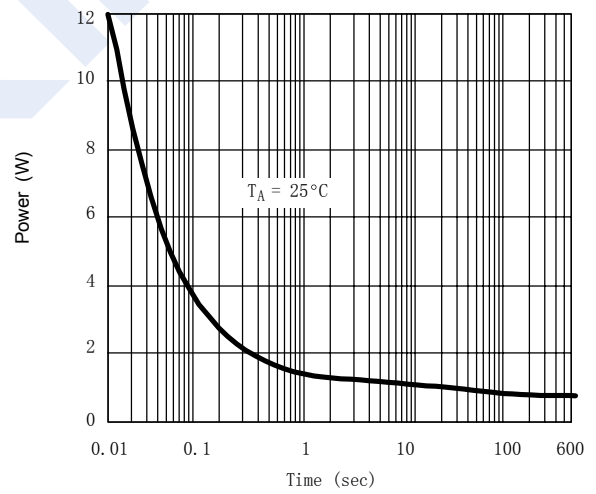
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

